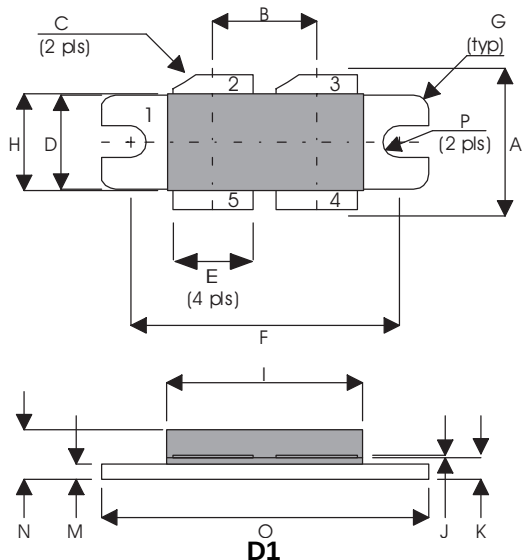


MECHANICAL DATA


PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1
 PIN 3 DRAIN 2 PIN 4 GATE 2
 PIN 5 GATE 1

DIM	Millimetres	Tol.	Inches	Tol.
A	15.24	0.50	0.600	0.020
B	10.80	0.13	0.425	0.005
C	45°	5°	45°	5°
D	9.78	0.13	0.385	0.005
E	8.38	0.13	0.330	0.005
F	27.94	0.13	1.100	0.005
G	1.52R	0.13	0.060R	0.005
H	10.16	0.15	0.400	0.006
I	21.84	0.23	0.860	0.009
J	0.10	0.02	0.004	0.001
K	1.96	0.13	0.077	0.005
M	1.02	0.13	0.040	0.005
N	4.45	0.38	0.175	0.015
O	34.04	0.13	1.340	0.005
P	1.63R	0.13	0.064R	0.005

GOLD METALLISED
MULTI-PURPOSE SILICON
DMOS RF FET
150W – 28V – 500MHz
PUSH-PULL
FEATURES

- SUITABLE FOR BROAD BAND APPLICATIONS
- SIMPLE BIAS CIRCUITS
- ULTRA-LOW THERMAL RESISTANCE
- BeO FREE
- LOW Crss
- HIGH GAIN – 12 dB MINIMUM

APPLICATIONS

- VHF/UHF COMMUNICATIONS
from 1 MHz to 500 MHz

P_D	Power Dissipation	648W (389W -A Version)
BV_{DSS}	Drain – Source Breakdown Voltage *	70V
BV_{GSS}	Gate – Source Breakdown Voltage*	±20V
$I_{D(sat)}$	Drain Current*	20A
T_{stg}	Storage Temperature	–65 to 150°C
T_j	Maximum Operating Junction Temperature	200°C

* Per Side

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
PER SIDE					
B _V DSS	Drain–Source Breakdown Voltage V _{GS} = 0 I _D = 100mA	70			V
I _D DSS	Zero Gate Voltage Drain Current V _{DS} = 28V V _{GS} = 0			4	mA
I _G DSS	Gate Leakage Current V _{GS} = 20V V _{DS} = 0			1	μA
V _{GS(th)}	Gate Threshold Voltage* I _D = 10mA V _{DS} = V _{GS}	1		7	V
g _{fs}	Forward Transconductance* V _{DS} = 10V I _D = 4A	3.2			mhos
V _{GS(th)match}	Gate Threshold Voltage Matching Between Sides I _D = 1A V _{DS} = V _{GS}			0.1	V
TOTAL DEVICE					
G _{PS}	Common Source Power Gain P _O = 150W	12			dB
η	Drain Efficiency V _{DS} = 28V I _{DQ} = 2A	50			%
VSWR	Load Mismatch Tolerance f = 400MHz	20:1			—
PER SIDE					
C _{iss}	Input Capacitance V _{DS} = 28V V _{GS} = –5V f = 1MHz			240	pF
C _{oss}	Output Capacitance V _{DS} = 28V V _{GS} = 0 f = 1MHz			100	pF
C _{rss}	Reverse Transfer Capacitance V _{DS} = 28V V _{GS} = 0 f = 1MHz			10	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 0.27°C / W 0.45 °C / W -A Version
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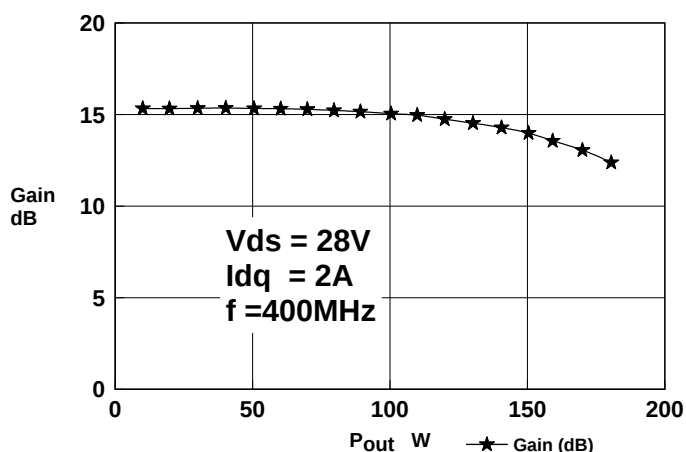


Figure 1 – Gain vs. Power Output.

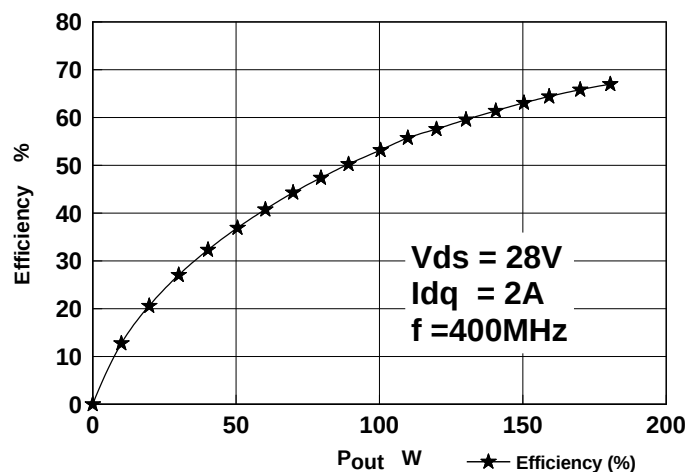


Figure 2 – Efficiency vs. Power Output.

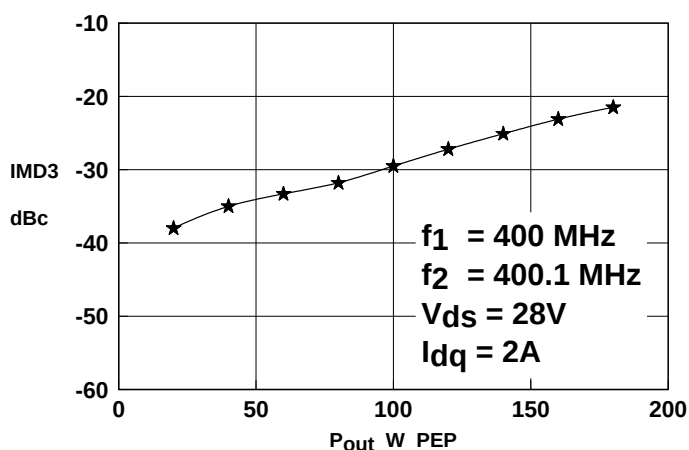


Figure 3 – IMD vs. Power Output

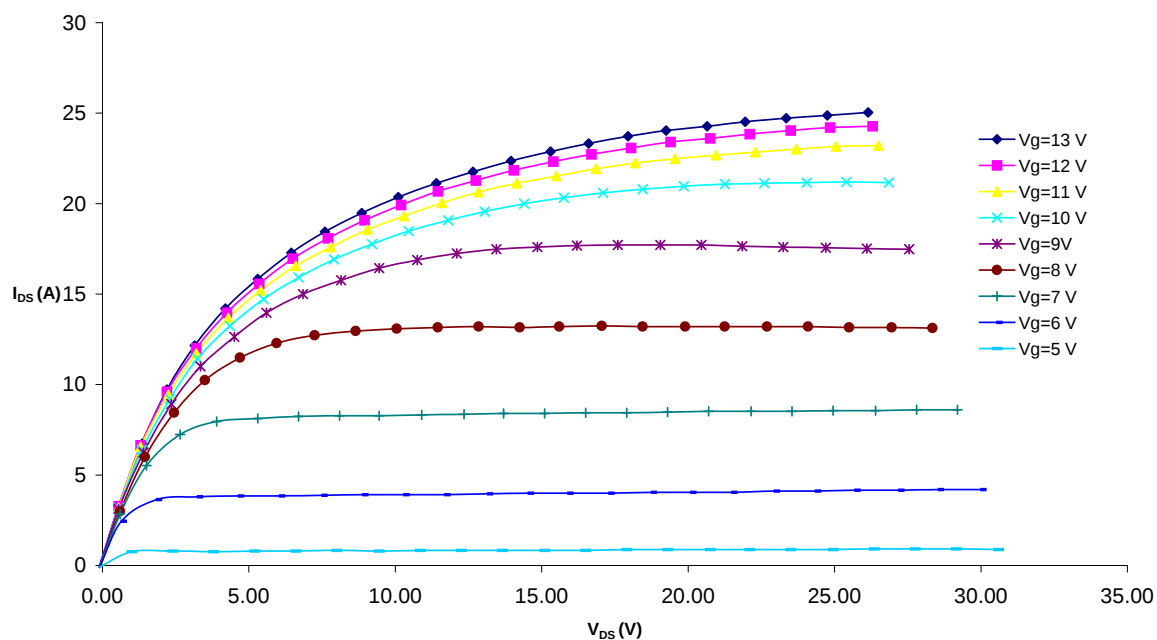


Figure 4 – Typical IV Characteristics.

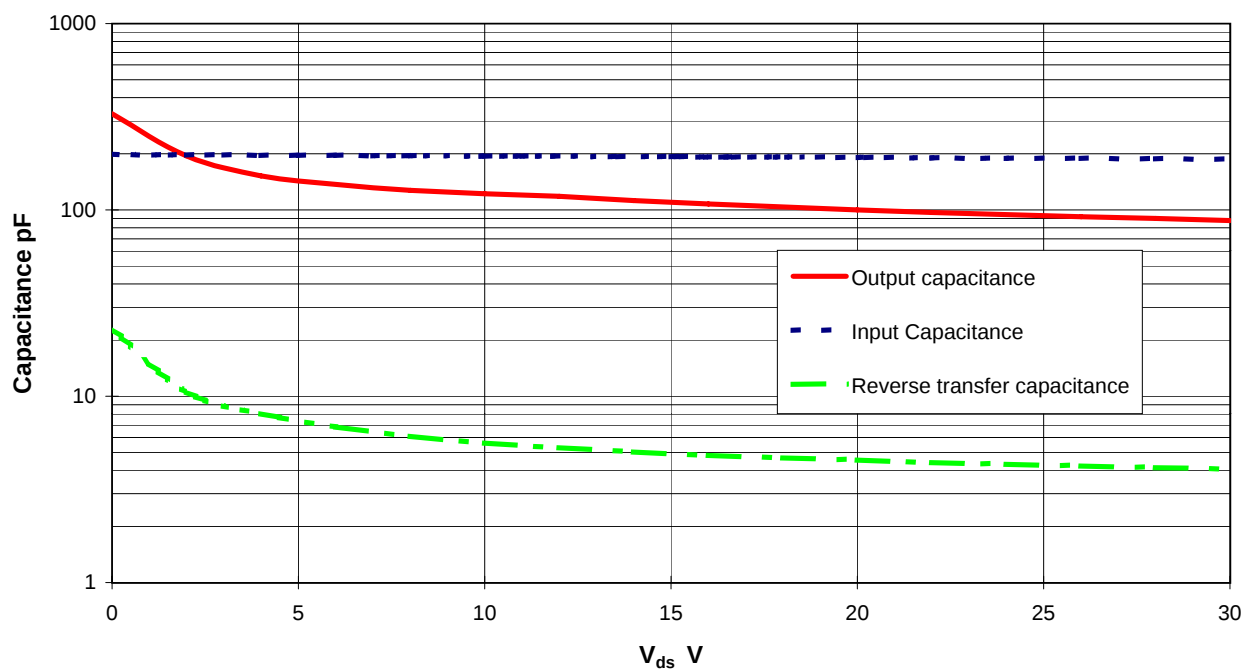
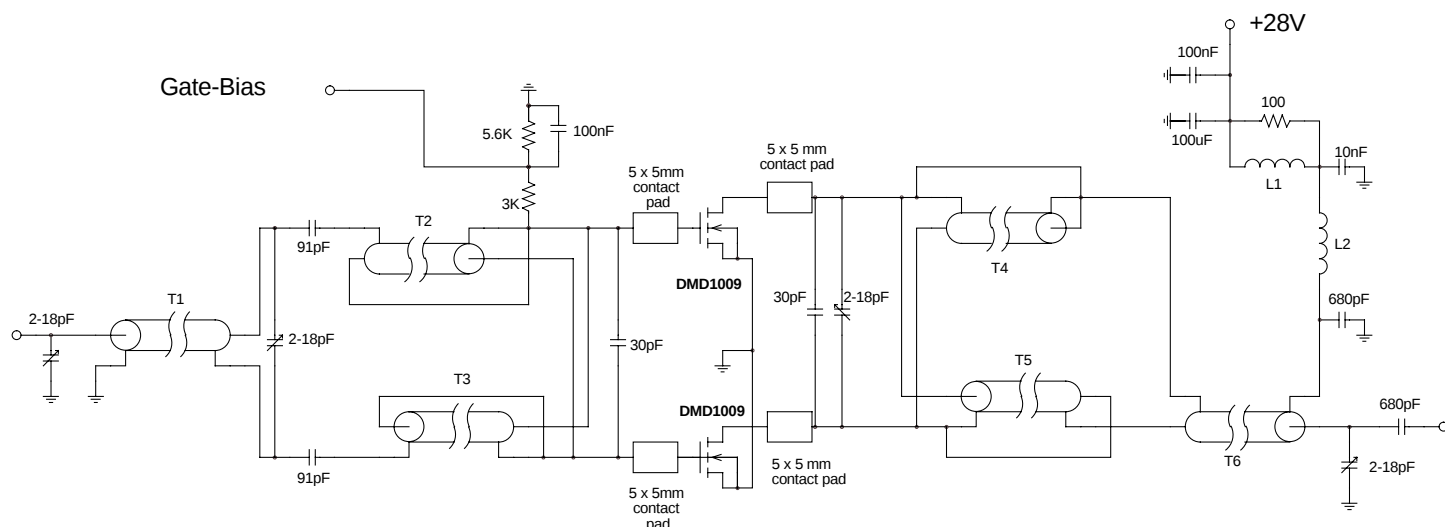


Figure 5 – Typical CV Characteristics.



DMD1009 TEST FIXTURE

Substrate 1.6mm PTFE/ glass, $\epsilon_r = 2.5$
All microstrip lines $W = 4.4\text{mm}$

T1	12cm	50 Ω UT85 semi-rigid coax on ferrite core
T2,3	7.5cm	15 Ω UT85-15 semi-rigid coax
T4,5	7cm	15 Ω UT85-15 semi-rigid coax
T6	11cm	50 Ω UT85 semi-rigid coax on ferrite core
L1	6.5 turns	25swg enamelled copper wire on Fair-Rite FT50B-43 core
L2	6.5 turns	25swg enamelled copper wire, 4mm internal diameter

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